

forming a photoresist film pattern on a semiconductor substrate  
excluding a first region;

performing a first halo implant process twice on the first region of the  
semiconductor substrate by using a tilt angle of about 45° and twist angles of  
0° and 180°; and

performing a second halo implant process on the first region of the  
semiconductor substrate by using a tilt angle of about 0°.

2. (Twice Amended) The method according to claim 1, wherein the first  
halo implant process is performed with an energy of 20KeV and a dose of  
 $4.0 \times 10^{12}$  ions/cm<sup>2</sup>.

---

4. (Twice Amended) The method according to claim 1, wherein the  
second halo implant process is performed only once at a tilt angle of about 0°.

5. (Twice Amended) The method according to claim 1, wherein the  
second halo implant process is performed with an energy of 16KeV and a dose  
of  $4 \times 10^{12}$  ions/cm<sup>2</sup>.

---

8. (Twice Amended) A method for forming a junction in a semiconductor  
device, comprising the steps of:

providing a semiconductor substrate divided into a first conductive type MOS region and a second conductive type MOS region;

forming a photoresist film pattern on the second conductive type MOS region;

*C3  
impl.* performing first and second halo implant processes on the first conductive type MOS region at about a 45° tilt angle and at twist angles of about 0° and 180°, respectively; and

performing a third halo implant process on the first conductive type MOS region, by using a tilt angle of about 0°.

---